

# **FDN5618P**

# 60V P-Channel Logic Level PowerTrench® MOSFET

## **General Description**

This 60V P-Channel MOSFET uses Fairchild's high voltage PowerTrench process. It has been optimized for power management applications.

# **Applications**

- DC-DC converters
- Load switch
- Power management

### **Features**

- -1.25 A, -60 V.  $R_{DS(ON)}$  = 0.170  $\Omega$  @  $V_{GS}$  = -10 V  $R_{DS(ON)}$  = 0.230  $\Omega$  @  $V_{GS}$  = -4.5 V
- · Fast switching speed
- High performance trench technology for extremely low  $R_{\mbox{\scriptsize DS}(\mbox{\scriptsize ON})}$



Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{\text{DSS}}$	Drain-Source Voltage	-60	V
V <sub>GSS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current - Continuous (Note 1a)	-1.25	Α
	– Pulsed	-10	
	Maximum Power Dissipation (Note 1a)	0.5	W
$P_D$	(Note 1b)	0.46	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

## **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	250	°C/W
R <sub>eJC</sub>	Thermal Resistance, Junction-to-Case	(Note 1)	75	°C/W

**Package Marking and Ordering Information** 

Device Marking	Device	Reel Size	Tape width	Quantity
618	FDN5618P	7"	8mm	3000 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	racteristics					
BV <sub>DSS</sub>	Drain–Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-60			V
ΔBV <sub>DSS</sub> ΔT <sub>.1</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = -250 $\mu$ A,Referenced to 25°C		-58		mV/°C
DSS	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -48 V, V <sub>GS</sub> = 0 V			-1	μΑ
GSSF	Gate-Body Leakage, Forward	$V_{GS} = 20V$ , $V_{DS} = 0 V$			100	nA
GSSR	Gate-Body Leakage, Reverse	$V_{GS} = -20 \text{ V}$ $V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	<b>–</b> 1	-1.6	-3	V
$\Delta V_{GS(th)} \over \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	$I_D$ = -250 $\mu$ A,Referenced to 25°C		4		mV/°C
R <sub>DS(on)</sub>	Static Drain–Source On–Resistance	$V_{GS} = -10 \text{ V},  I_D = -1.25 \text{ A}$ $V_{GS} = -4.5 \text{ V},  I_D = -1.0 \text{ A}$ $V_{GS} = -10 \text{ V}, I_D = -3 \text{ A} \text{ T}_J = 125^{\circ}\text{C}$	0	0.148 0.185 0.245	0.170 0.230 0.315	Ω
I <sub>D(on)</sub>	On–State Drain Current	$V_{GS} = -10 \text{ V}, \qquad V_{DS} = -5 \text{ V}$	<b>–</b> 5			Α
g <sub>FS</sub>	Forward Transconductance	$V_{DS} = -5 \text{ V}, \qquad I_{D} = -1.25 \text{ A}$	-	4.3		S
Dynamio	Characteristics	2 13				
C <sub>iss</sub>	Input Capacitance	$V_{DS} = -30 \text{ V},  V_{GS} = 0 \text{ V},$		430		pF
Coss	Output Capacitance	f = 1.0 MHz		52		pF
Crss	Reverse Transfer Capacitance			19		pF
Switchir	ng Characteristics (Note 2)					
d(on)	Turn-On Delay Time	$V_{DD} = -30 \text{ V}, \qquad I_{D} = -1 \text{ A}, \\ V_{GS} = -10 \text{ V}, \qquad R_{GEN} = 6 \Omega$		6.5	13	ns
г	Turn-On Rise Time	$V_{GS} = -10 \text{ V}, \qquad R_{GEN} = 6 \Omega$		8	16	ns
d(off)	Turn-Off Delay Time			16.5	30	ns
f	Turn-Off Fall Time			4	8	ns
$Q_g$	Total Gate Charge	$V_{DS} = -30 \text{ V}, \qquad I_{D} = -1.25 \text{ A},$		8.6	13.8	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = -10 V		1.5		nC
$Q_{gd}$	Gate-Drain Charge	7		1.3		nC
Drain–S	ource Diode Characteristics a	and Maximum Ratings				
ls	Maximum Continuous Drain–Source				-0.42	Α
V <sub>SD</sub>	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V},  I_S = -0.42  \text{(Note 2)}$		-0.7	-1.2	V

#### Notes:

 R<sub>B,IA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>B,IC</sub> is guaranteed by design while R<sub>B,CA</sub> is determined by the user's board design.



a) 250°C/W when mounted on a 0.02 in² pad of 2 oz. copper.

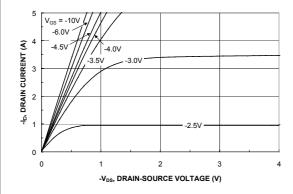


b) 270°C/W when mounted on a minimum pad.

Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width  $\leq 300~\mu\text{s},~\text{Duty Cycle} \leq 2.0$ 

# **Typical Characteristics**



2.2 Postors 1.8 Po

Figure 1. On-Region Characteristics.

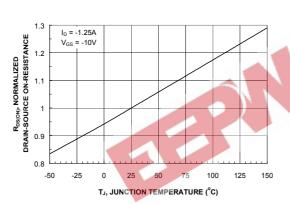


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

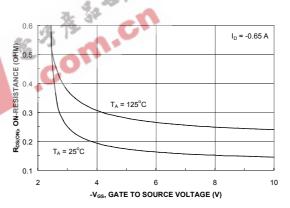


Figure 3. On-Resistance Variation withTemperature.

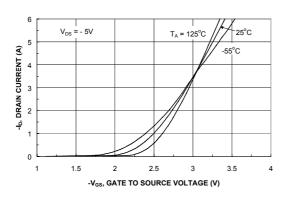


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

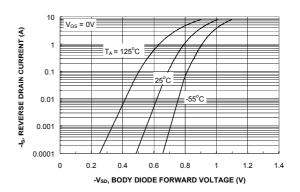
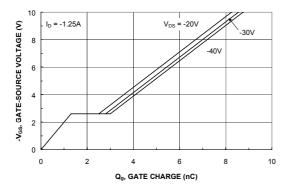


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

# **Typical Characteristics**



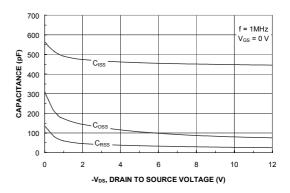


Figure 7. Gate Charge Characteristics.

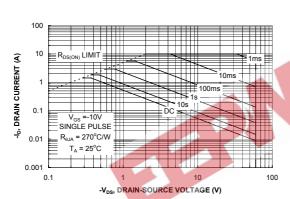


Figure 8. Capacitance Characteristics.

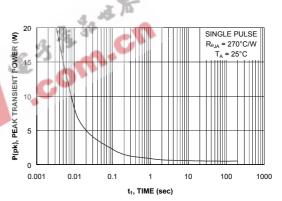


Figure 9. Maximum Safe Operating Area.



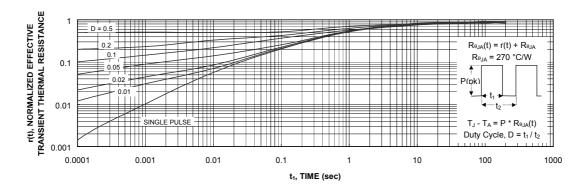
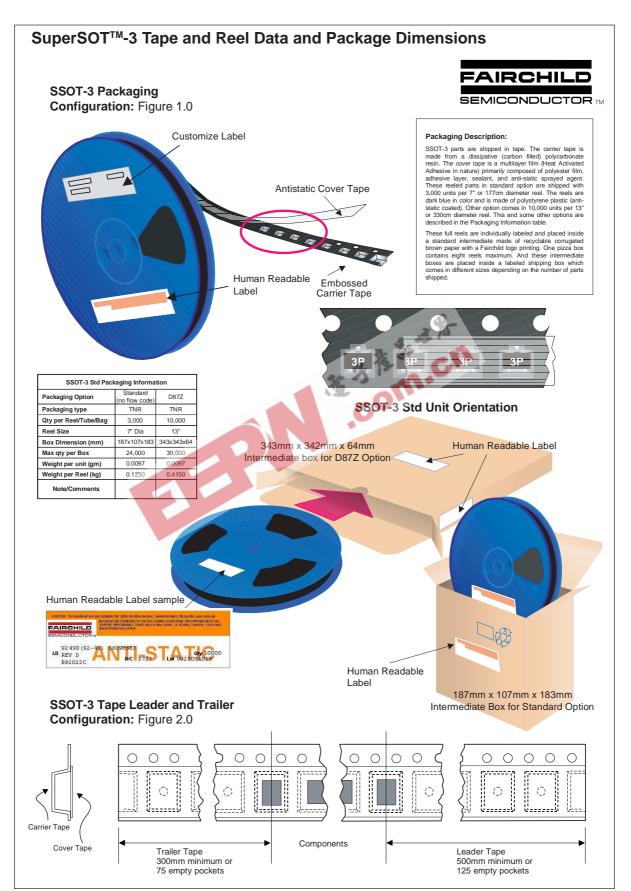
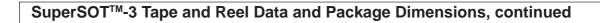


Figure 11. Transient Thermal Response Curve.

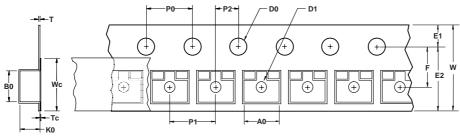
Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.





## **SSOT-3 Embossed Carrier Tape**

Configuration: Figure 3.0



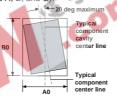
User Direction of Feed	
	$\overline{}$

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
SSOT-3 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-02

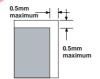
Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View Component Rotation



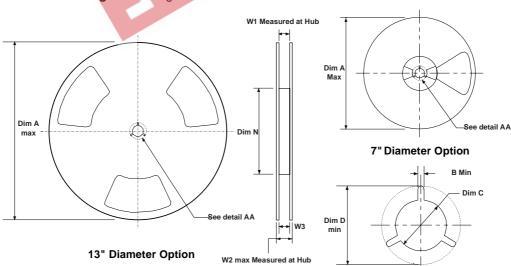
Sketch B (Top View)
Component Rotation



Sketch C (Top View)

Component lateral movement

## SSOT-3 Reel Configuration: Figure 4.0



								DETAIL AA	ı
	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

# SuperSOT™-3 Tape and Reel Data and Package Dimensions, continued SuperSOT™-3 (FS PKG Code 32) Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters] Part Weight per unit (gram): 0.0097 -0.0990±0.0050 [2.51±0.13] -0.1150±0.0050 [2.92±0.13] 0.0550±0.0030 [1.40±0.08] 0.0900 [2.29] -0.0375±0.0025 [0.95±0.06] 0.0300 [0.76]TYP. 0.0240 0.61 0.0180 0.46 -0.0375 [0.95] LAND PATTERN RECOMMENDATION R0.0030 [R0.08]MIN. TYP. GAGE PLANE \_0.0365 [0.93] 0.0070 R0.0030 [R0.08]MIN. TYP. 0.0015 [0.038] C 0.0150±0.0020 [0.38±0.05]-0.0080 [0.20]-0.0040 0.10 TYP.-0.0175±0.0025 [0.44±0.06]TYP. -SEATING PLANE $0.0220_{-0.0040}^{+0.0020}$ $0.56_{-0.10}^{+0.05}$ TYP. NOTES: UNLESS OTHERWISE SPECIFIED SUPER SOT , 3 LEADS 1. STANDARD LEAD FINISH TO BE 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN/LEAD (SOLDER) ON COPPER. 2. NO JEDEC REGISTRATION AS OF DEC. 1995.

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